

<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)</b>		ATTY. DOCKET NO. 006301 USA/ Consilium/Consilium	SERIAL NO. 09/928,474			
		APPLICANT Badri N. KRISHNAMURTHY et al.				
		FILING DATE August 14, 2001	GROUP 2812			
<b>U.S. PATENT DOCUMENTS</b>						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>AS</i>	6,303,395 B1	10/16/01	Nulman			06/01/99
<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>						
<i>AS</i>	September 16, 2004. International Preliminary Examination Report for PCT Serial No. PCT/US02/24859.					
EXAMINER <i>Andrea O'Flaherty</i>	DATE CONSIDERED <i>12/07/04</i>					

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SHEET 2 OF 7

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EXAMINER <i>Andrea C. Havemann</i>			DATE CONSIDERED <i>12/07/04</i>			

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